

n-channel JFET designed for . . .



Performance Curves NH
See Section 4

- VHF/UHF Amplifier
- Oscillators
- Mixers

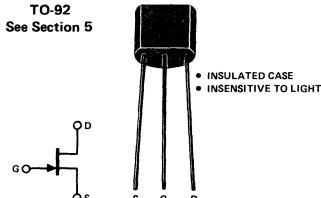
BENEFITS

- Specified for 100 MHz and 400 MHz Operation
- Low Cost
- Automated Insertion Package

ABSOLUTE MAXIMUM RATINGS

Drain-Source Voltage	30 V
Drain-Gate Voltage	30 V
Reverse Gate-Source Voltage	-30 V
Forward Gate Current	50 mA
Total Device Dissipation @ 25°C	360 mW
Derate above 25°C	2.88 mW/°C
Storage Temperature Range	-65 to +150°C
Operating Junction Temperature Range	-55 to +125°C
Lead Temperature (1/16" from case for 10 seconds)	260°C

TO-92
See Section 5



ELECTRICAL CHARACTERISTICS (25°C unless otherwise noted)

Characteristic		Min	Max	Unit	Test Conditions
1 S	BVGSS Gate-Source Breakdown Voltage	-30		V	$I_G = -1 \mu A, V_{DS} = 0$
2 T	I_{GSS} Gate Reverse Current	-1.0		nA	
3 A		-0.5		μA	$V_{GS} = -20 V, V_{DS} = 0, T_A = 100^\circ C$
4 C	$V_{GS(off)}$ Gate-Source Cutoff Voltage	-1	-6	V	$V_{DS} = 15 V, I_D = 10 nA$
5	I_{DSS} Saturation Drain-Current (Note 1)	5	15	mA	$V_{DS} = 15 V, V_{GS} = 0$
6	$ Y_{fs} $ Common-Source Forward Transfer Admittance	4.5	7.5	mmho	$V_{DS} = 15 V, V_{GS} = 0, f = 1 kHz$
7	$ Y_{os} $ Common-Source Output Admittance	0.05		mmho	$V_{DS} = 15 V, V_{GS} = 0, f = 1 kHz$
8	C_{iss} Common-Source Input Capacitance	4.5		pF	
9	C_{rss} Common-Source Reverse Transfer Capacitance	1.0		pF	$V_{DS} = 15 V, V_{GS} = 0, f = 1 MHz$
10	$Re(Y_{is})$ Common-Source Input Conductance	0.1		mmho	
11	$Im(Y_{is})$ Common-Source Input Susceptance	3		mmho	
12	$Re(Y_{os})$ Common-Source Output Conductance	0.075		mmho	$V_{DS} = 15 V, V_{GS} = 0, f = 100 MHz$
13	$Im(Y_{os})$ Common-Source Output Susceptance	0.9		mmho	
14	$Re(Y_{is})$ Common-Source Input Conductance	1		mmho	
15	$Im(Y_{is})$ Common-Source Input Susceptance	12		mmho	
16	$Re(Y_{fs})$ Common-Source Forward Transfer Conductance	4		mmho	$V_{DS} = 15 V, V_{GS} = 0, f = 400 MHz$
17	$Re(Y_{os})$ Common-Source Output Conductance	0.1		mmho	
18	$Im(Y_{os})$ Common-Source Output Conductance	4		mmho	
19	G_{ps} Common-Source Neutralized Insertion Power Gain	18		dB	$V_{DS} = 15 V, I_D = 5 mA, f = 100 MHz$
20		10		dB	$f = 400 MHz$
21	NF Noise Figure		2	dB	$V_{DS} = 15 V, I_D = 5 mA, f = 100 MHz$
22			4	dB	$R_G = 1K \Omega, f = 400 MHz$

NOTE:

- Pulse tested: pulse width = 300 μs , duty cycle $\leq 2\%$.

NH